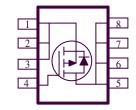
P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$			
	$60 @ V_{GS} = -4.5V$	-8.3			
-20	$80 @ V_{GS} = -2.5V$	-6.7			
	150 @ V _{GS} = -1.8V	-4.5			

- $\begin{tabular}{ll} \bullet & Low \ r_{DS(on)} \ provides \ higher \ efficiency \ and \\ extends \ battery \ life \end{tabular}$
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





RoHS
COMPLIANT
HALOGEN
FREE

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)							
Parameter			Maximum	Units			
Drain-Source Voltage			-20	V			
Gate-Source Voltage			±12	v			
Continuous Drain Current ^a	$T_A=25^{\circ}C$		-8.3				
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	-6.7	A			
Pulsed Drain Current ^b	I_{DM}	±50					
Continuous Source Current (Diode Conduction) ^a		I_S	-2.1	A			
D	$T_A=25^{\circ}C$	D	3.1	w			
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	L D	2.0	VV			
Operating Junction and Storage Temperature Range		T_{J}, T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum Unit				
	t <= 10 sec	D	40	°C/W		
Maximum Junction-to-Ambient ^a	Steady-State	$ m R_{ heta JA}$	70	°C/W		

1

Notes

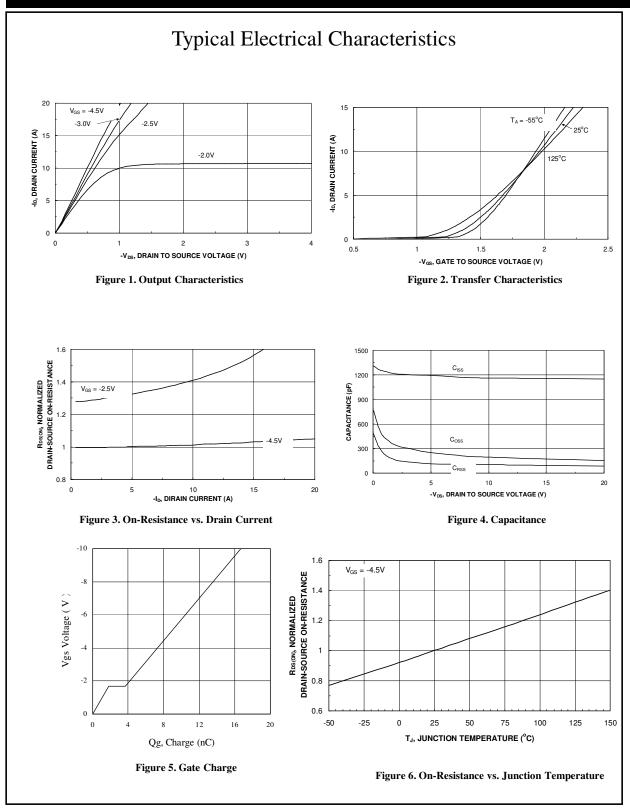
- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Downwoodor		TD 4 C 1141	Limits			T
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-0.7			
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
Zelo Cate voltage Diam current	1055	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -4.5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			Α
		$V_{GS} = -4.5 \text{ V}, I_D = -8.3 \text{ A}$			60	
Drain-Source On-Resistance ^A	rDS(on)	$V_{GS} = -2.5 \text{ V}, I_D = -6.7 \text{ A}$			80	mΩ
		$V_{GS} = -1.8 \text{ V}, I_D = -4.5 \text{ A}$			150	
Forward Tranconductance ^A	$g_{ m fs}$	$V_{DS} = -15 \text{ V}, I_D = -8.3 \text{ A}$		70		S
Diode Forward Voltage	V_{SD}	$I_S = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.6		V
Dynamic ^b						
Total Gate Charge	Q_{g}	V_{DS} = -10 V, V_{GS} = -4.5 V, I_{D} = -8.3 A		16.7		
Gate-Source Charge	Q_{gs}			1.8		nC
Gate-Drain Charge	Q_{gd}			1.9		
Turn-On Delay Time	t _{d(on)}			20		
Rise Time	$t_{ m r}$	$V_{DD} = -10 \text{ V}, R_L = 6 \Omega, ID = -1 \text{ A},$ VGEN = -4.5 V		23		nS
Turn-Off Delay Time	t _{d(off)}			289		
Fall-Time	t_{f}			134		

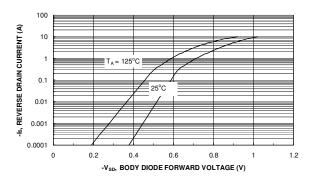
Notes

- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics



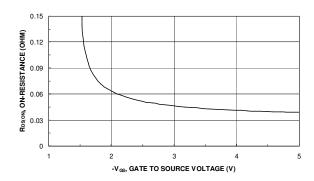
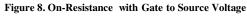
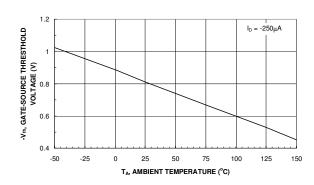


Figure 7. Source-Drain Diode Forward Voltage





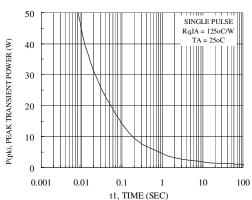


Figure 9. Vth Gate to Source Voltage Vs Temperature

Figure 10. Single Pulse Maximum Power Dissipation

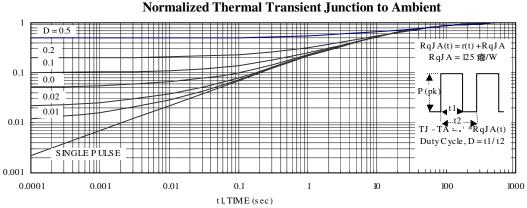
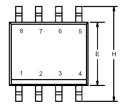
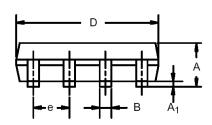


Figure 11. Transient Thermal Response Curve

Package Information

SO-8: 8LEAD





	MILLIM	MILLIMETERS INC		HES	
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	

